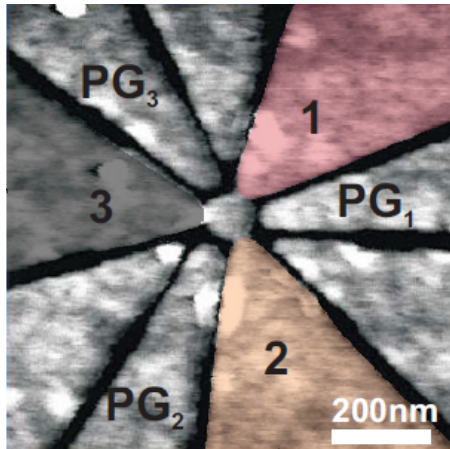


# Three-terminal graphene quantum devices



K. Ensslin



Solid State Physics **ETH Zürich**

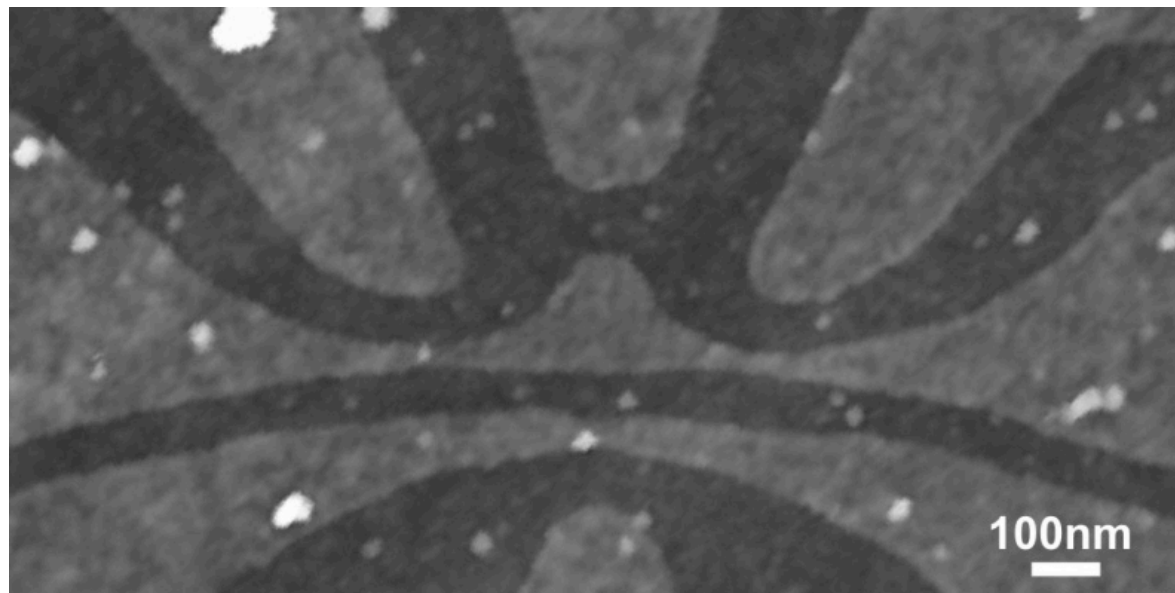
with

A. Jacobsen  
P. Simonet  
S. Dröscher  
C. Barraud  
T. Ihn

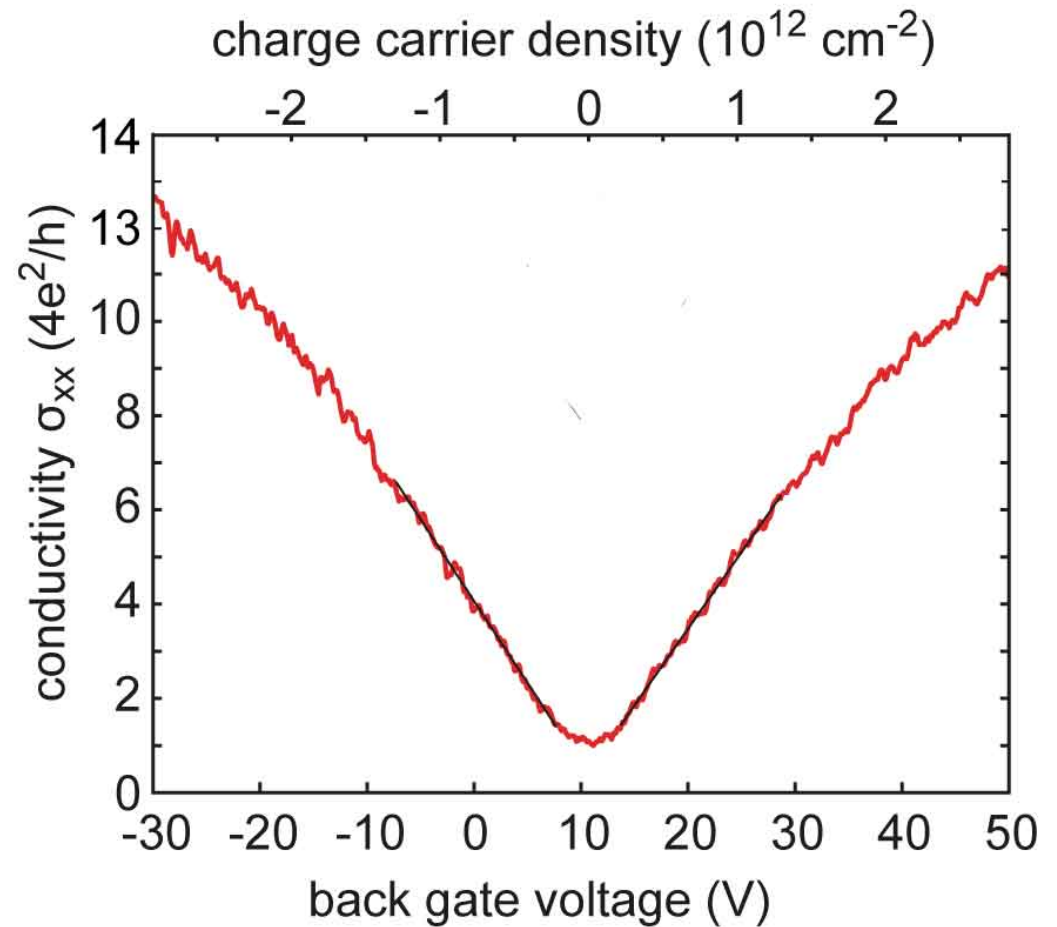
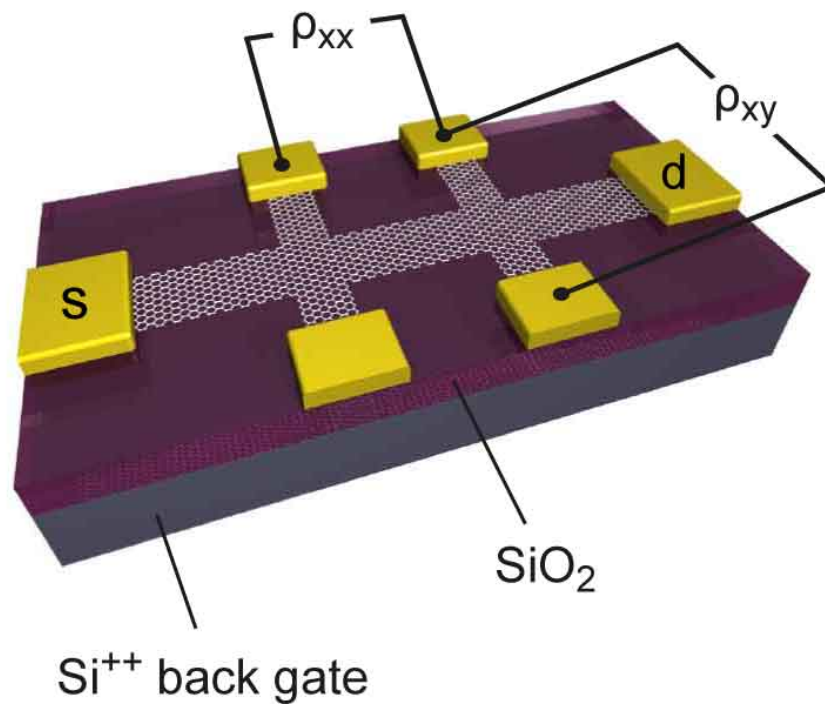
- constrictions and dots
- 3-terminal dots
- bilayer quantum structures

# Why graphene quantum devices?

- Lateral patterning -> quantum structures
- Finite lateral size -> quantum confinement (?)
- Spin qubits -> long spin coherence times (?)
  
- What controls the confinement?
- What are the relevant energy scales?

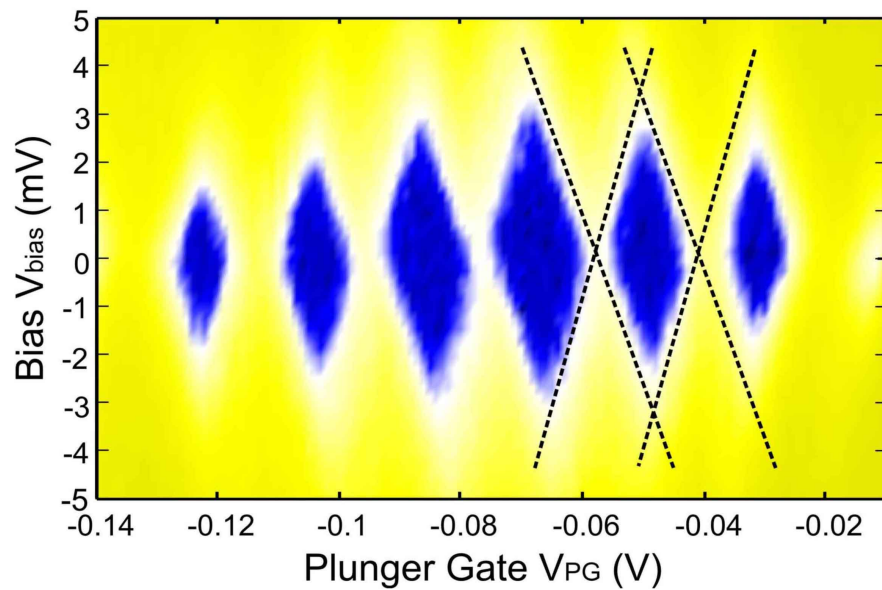
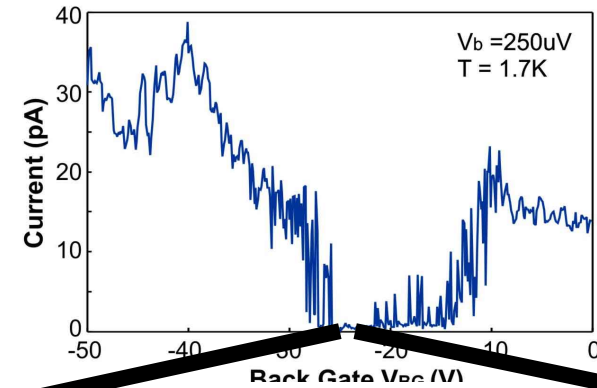
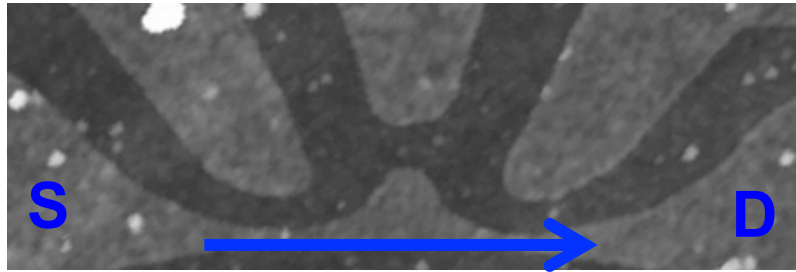


# Graphene Hall bars

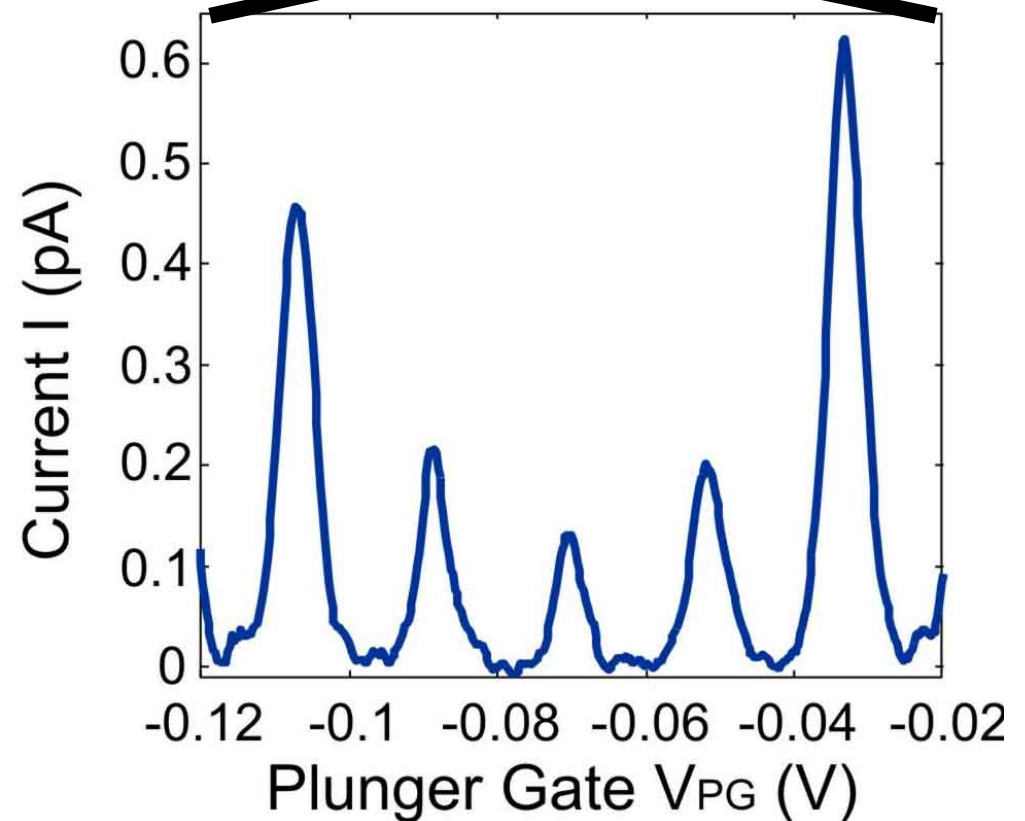


Conductivity is a  $\approx$  linear function of gate voltage

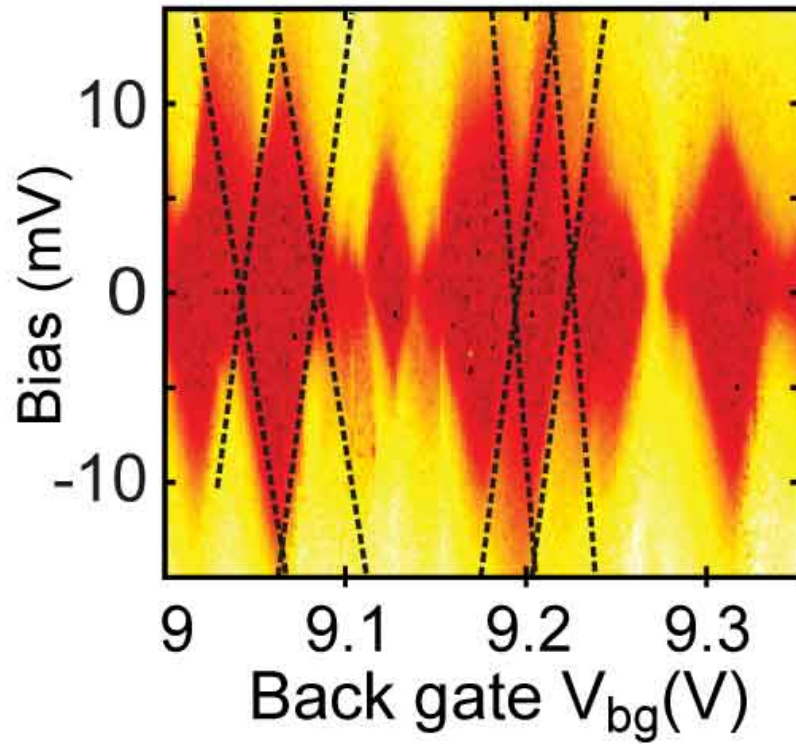
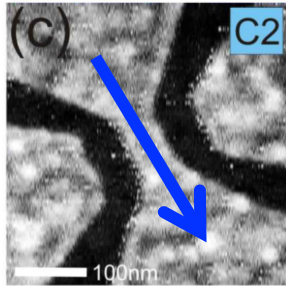
# Graphene quantum dots



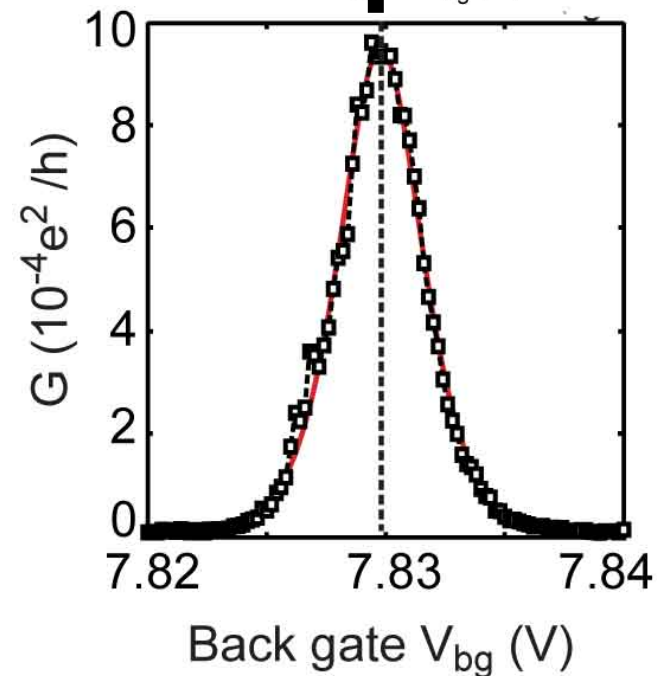
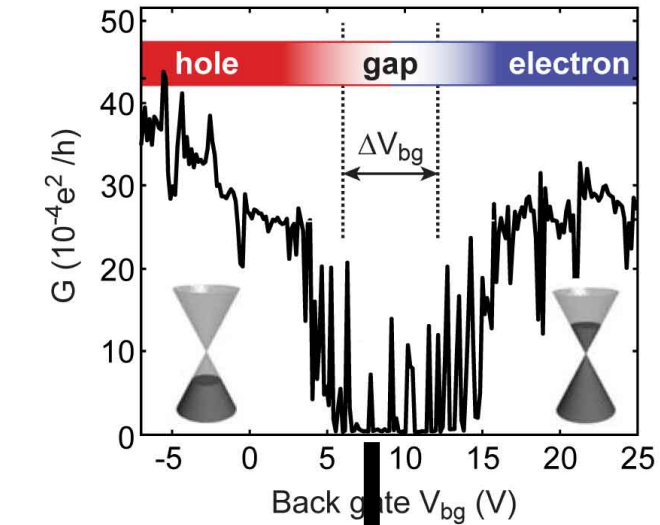
Coulomb blockade



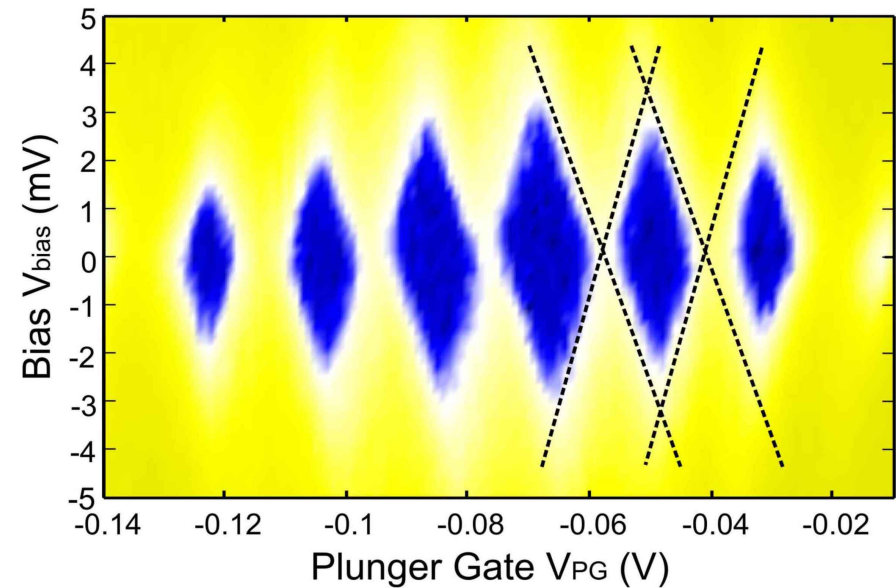
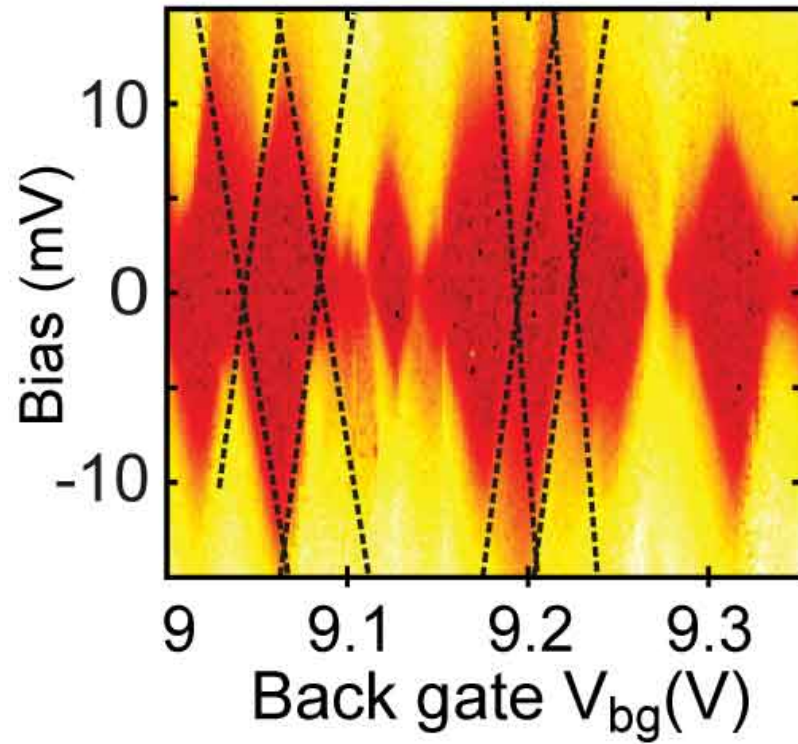
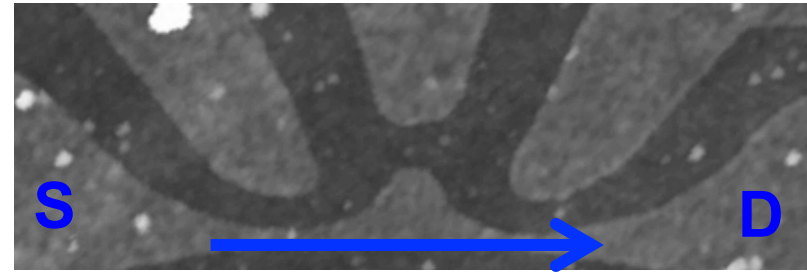
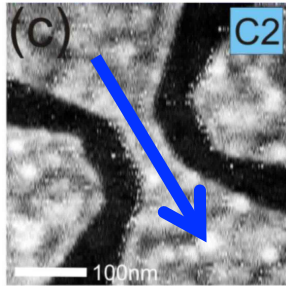
# But: Graphene constrictions



Coulomb blockade

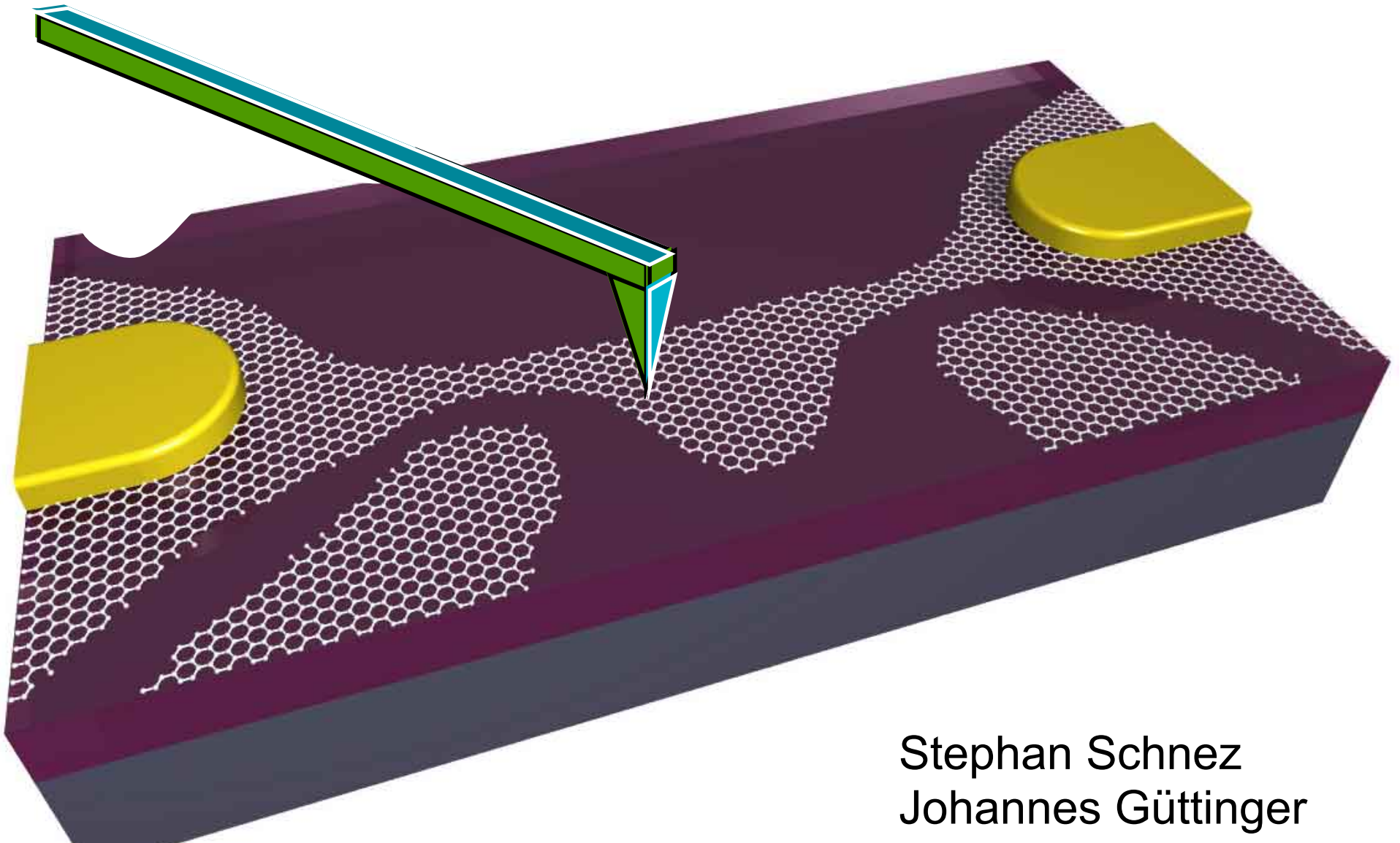


# Constrictions and dots



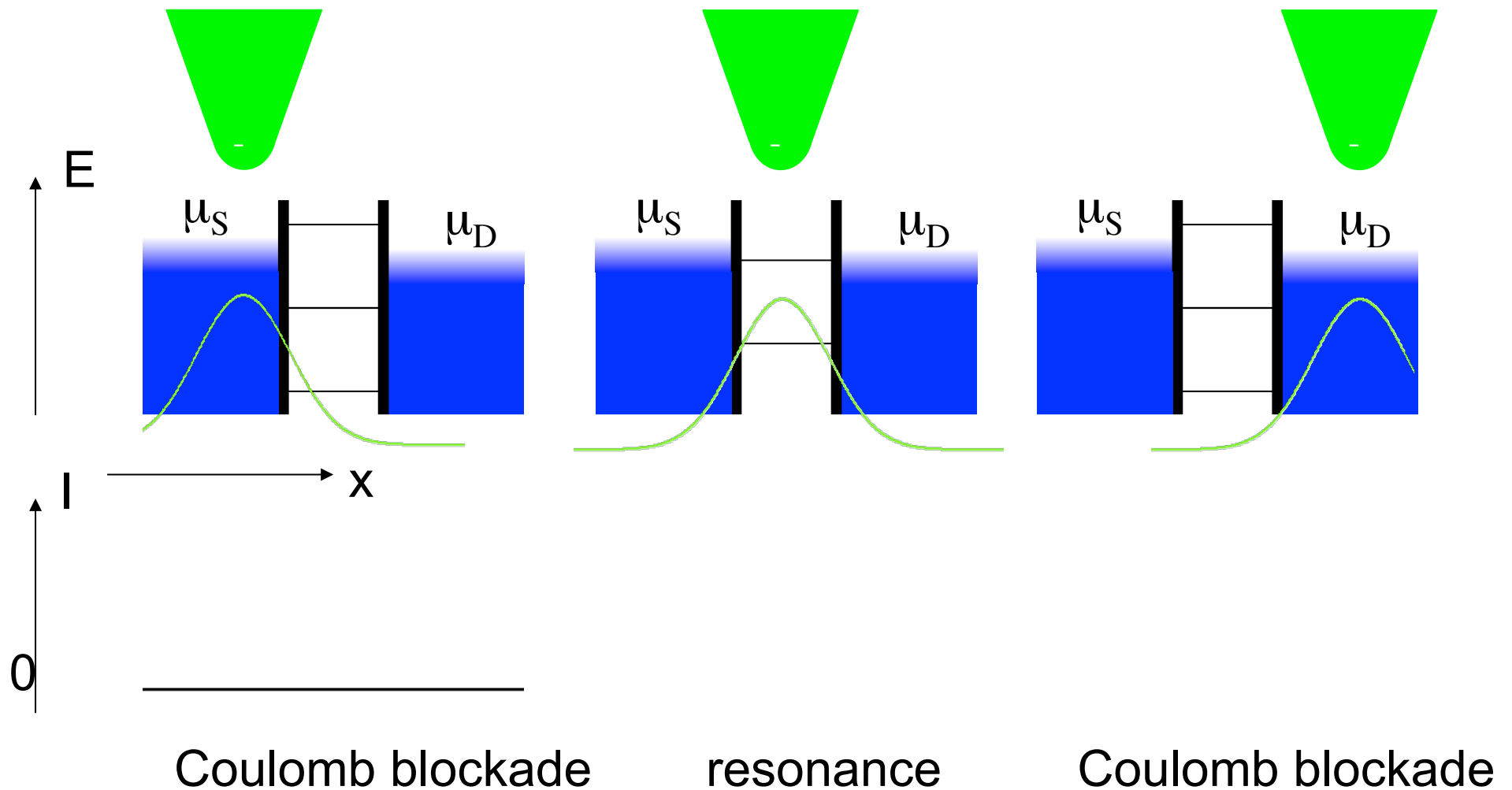
How to distinguish confined states in constrictions and dots?

# Scanning gate experiments



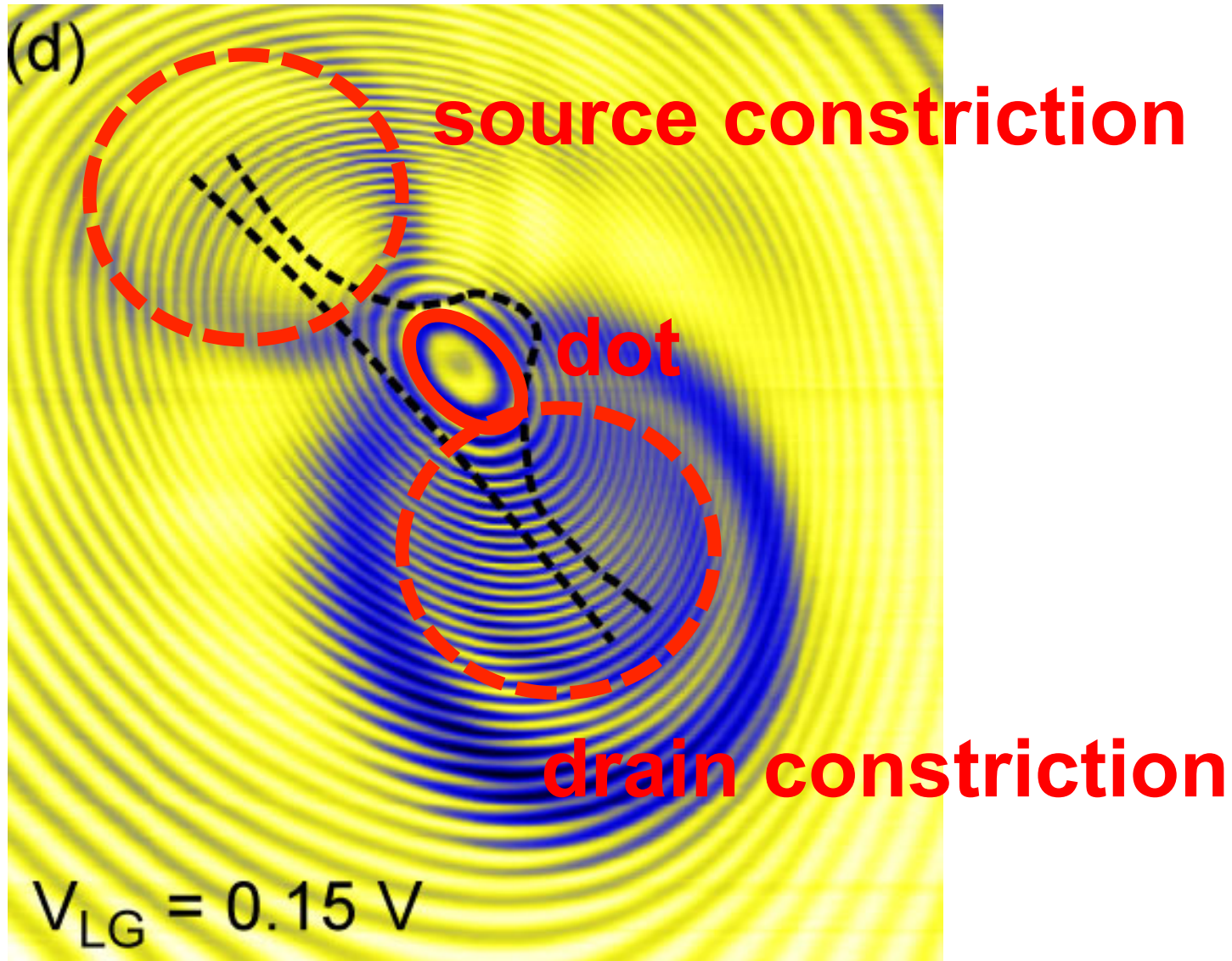
Stephan Schnez  
Johannes Güttinger

# Scanning the tip of an AFM across a quantum dot

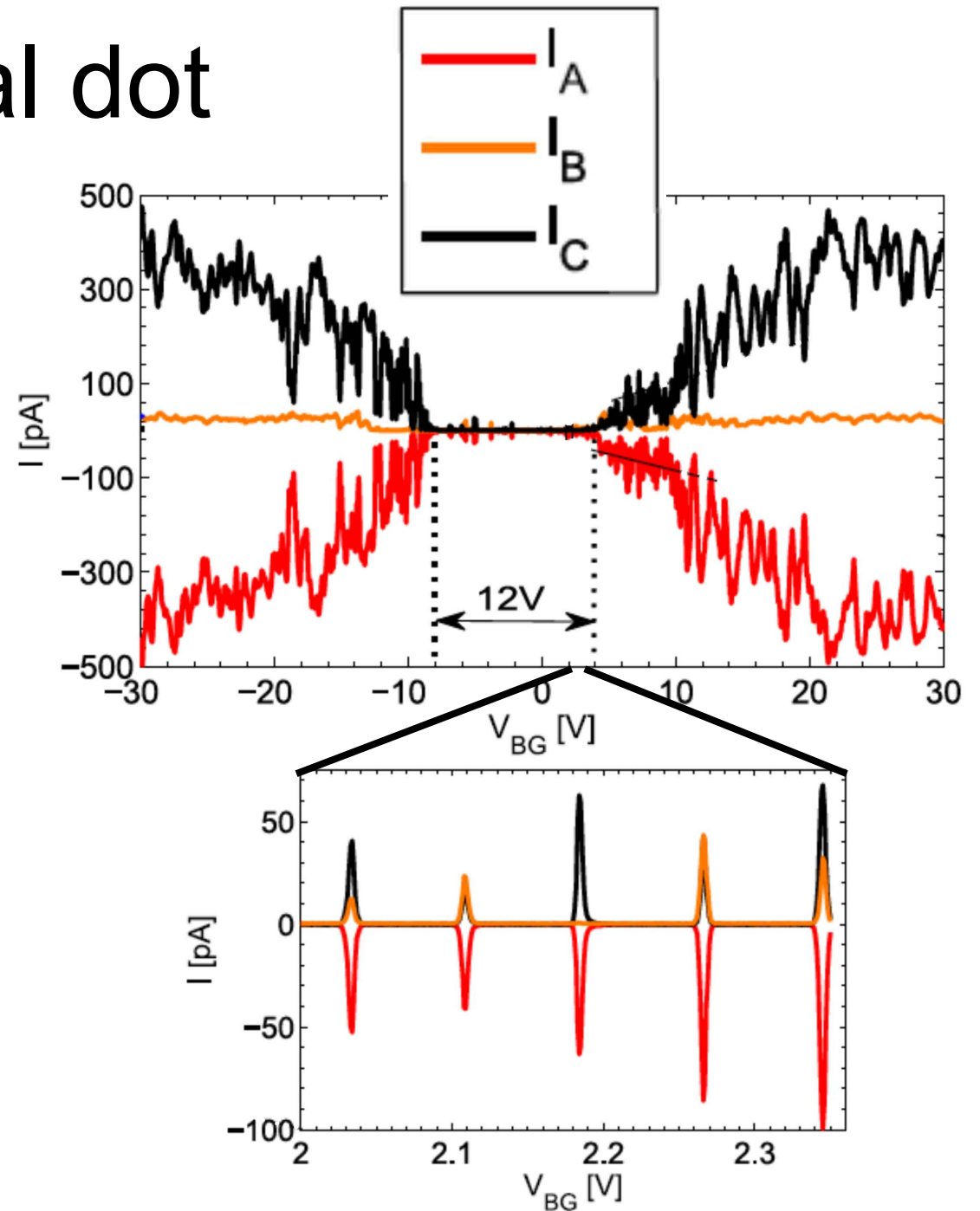
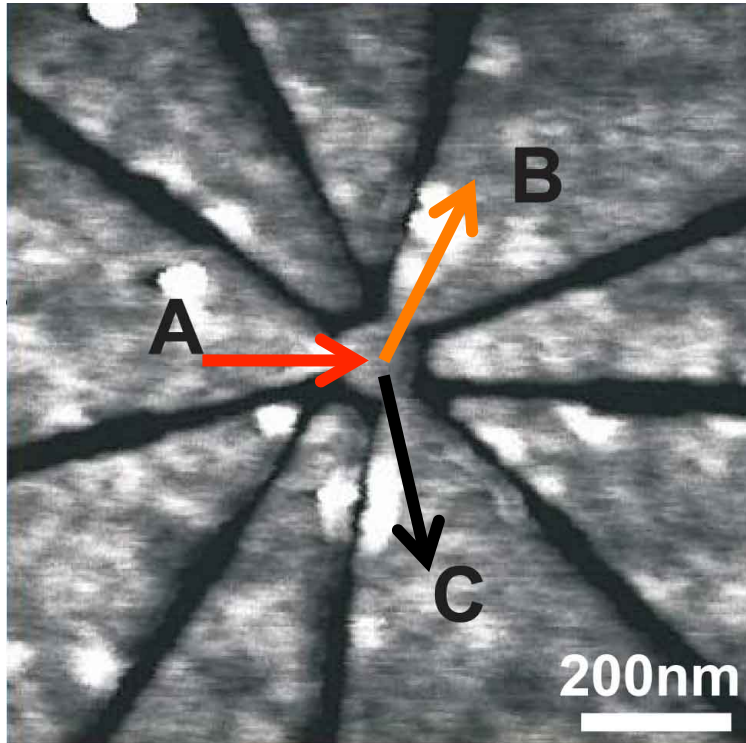




# Scanning gate experiments

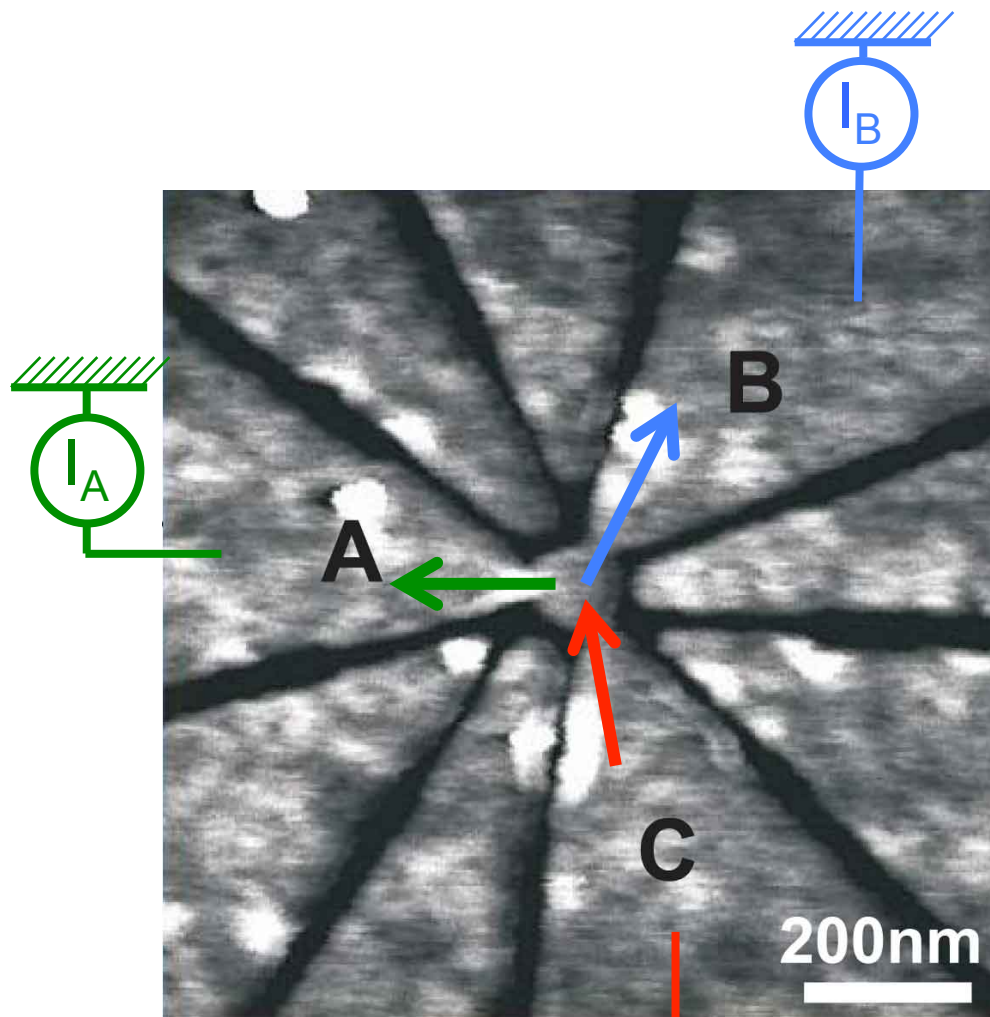


# Three-terminal dot

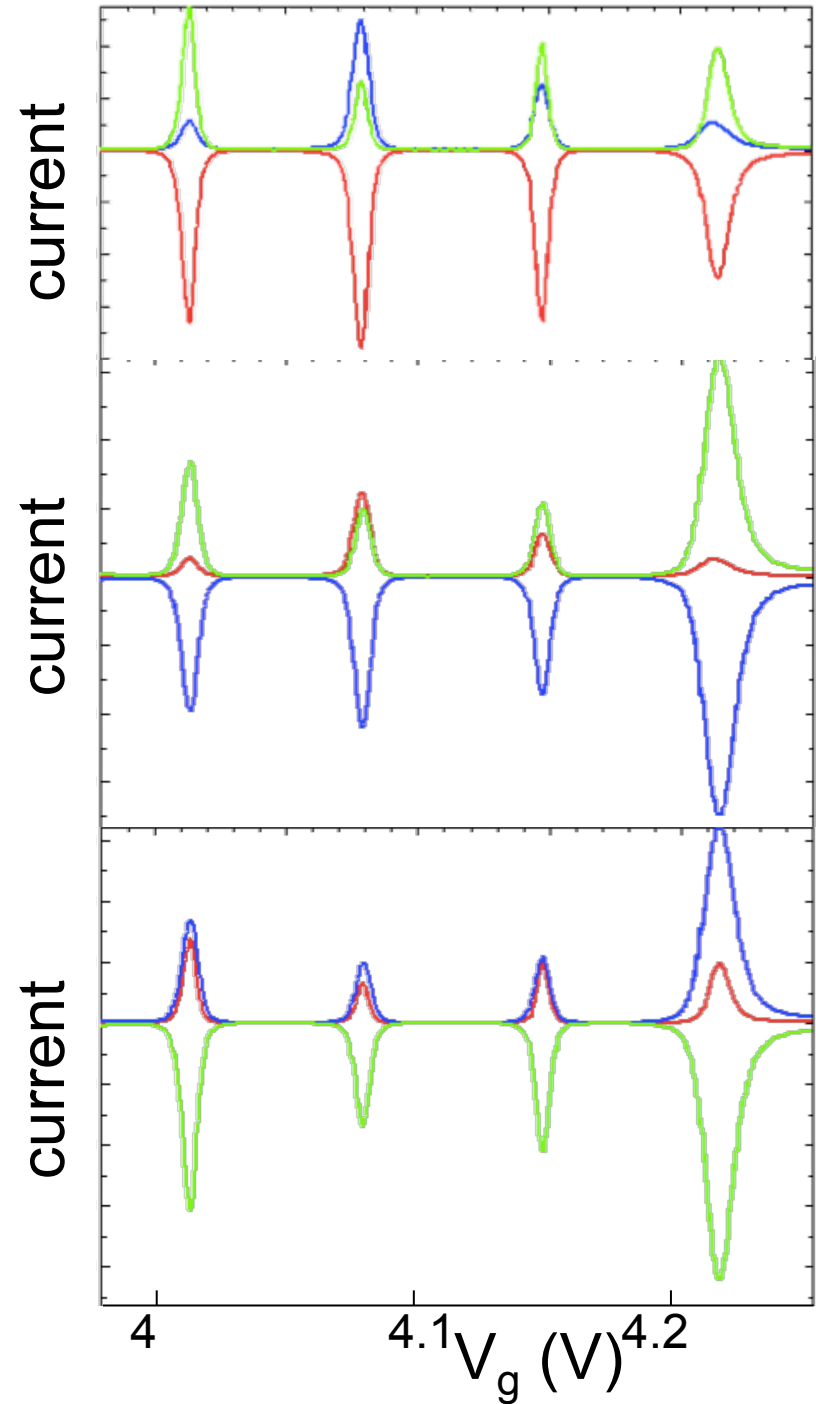
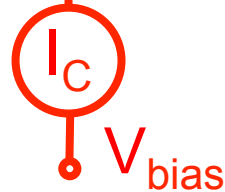


Arnhild Jacobsen  
Pauline Simonet

# Three-terminal dot



Arnhild Jacobsen  
Pauline Simonet



# Three-terminal dot

## conductance matrix

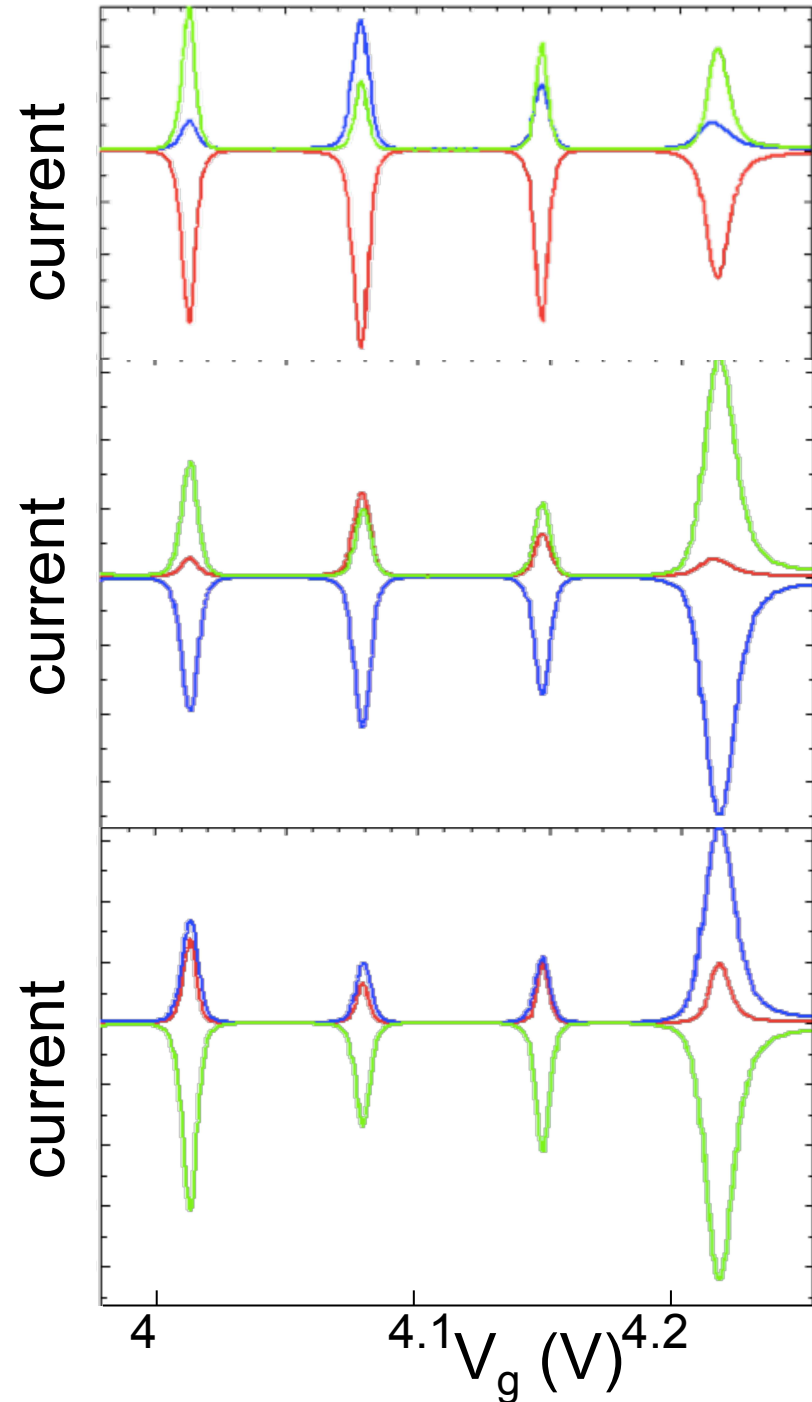
$$\begin{pmatrix} I_1 \\ I_2 \\ I_3 \end{pmatrix} = \begin{pmatrix} G_{11} & G_{12} & G_{13} \\ G_{21} & G_{22} & G_{23} \\ G_{31} & G_{32} & G_{33} \end{pmatrix} \begin{pmatrix} V_1 \\ V_2 \\ V_3 \end{pmatrix}$$

## sum rules

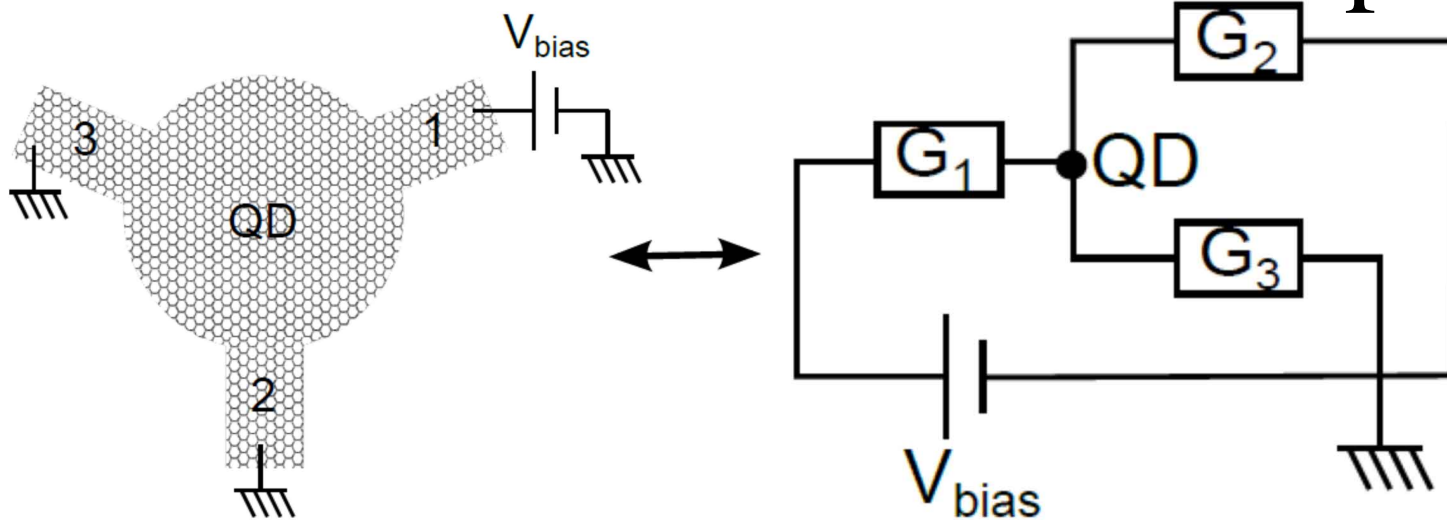
current conservation:

$$\sum I_i = 0 \rightarrow \sum_{i=1}^3 G_{ij} = 0$$

$$V_1 = V_2 = V_3 \rightarrow I_i = 0 \rightarrow \sum_{j=1}^3 G_{ij} = 0$$



# measurement set-up



Kirchhoff rules

apply voltage to one terminal  
measure current in three terminals

$G_{ij}$ : three-terminal conductance  
 $G_i$ : lead conductance

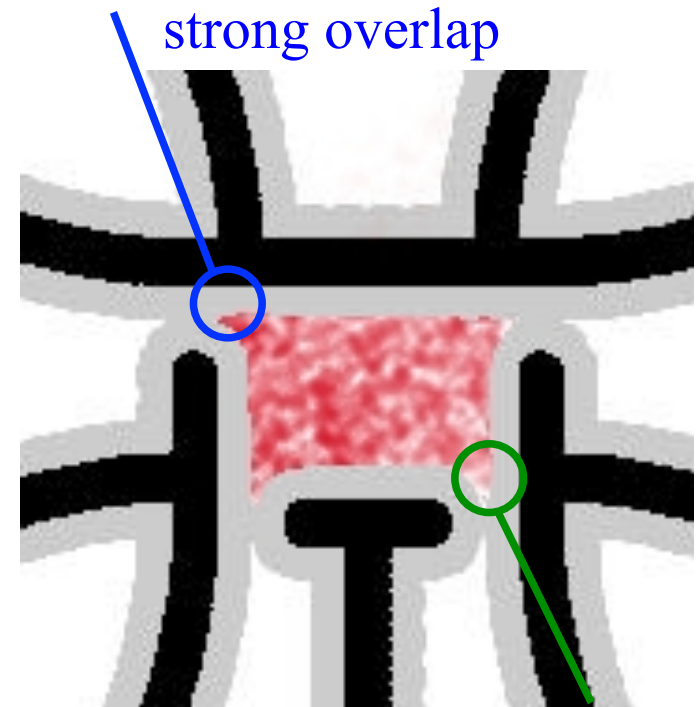
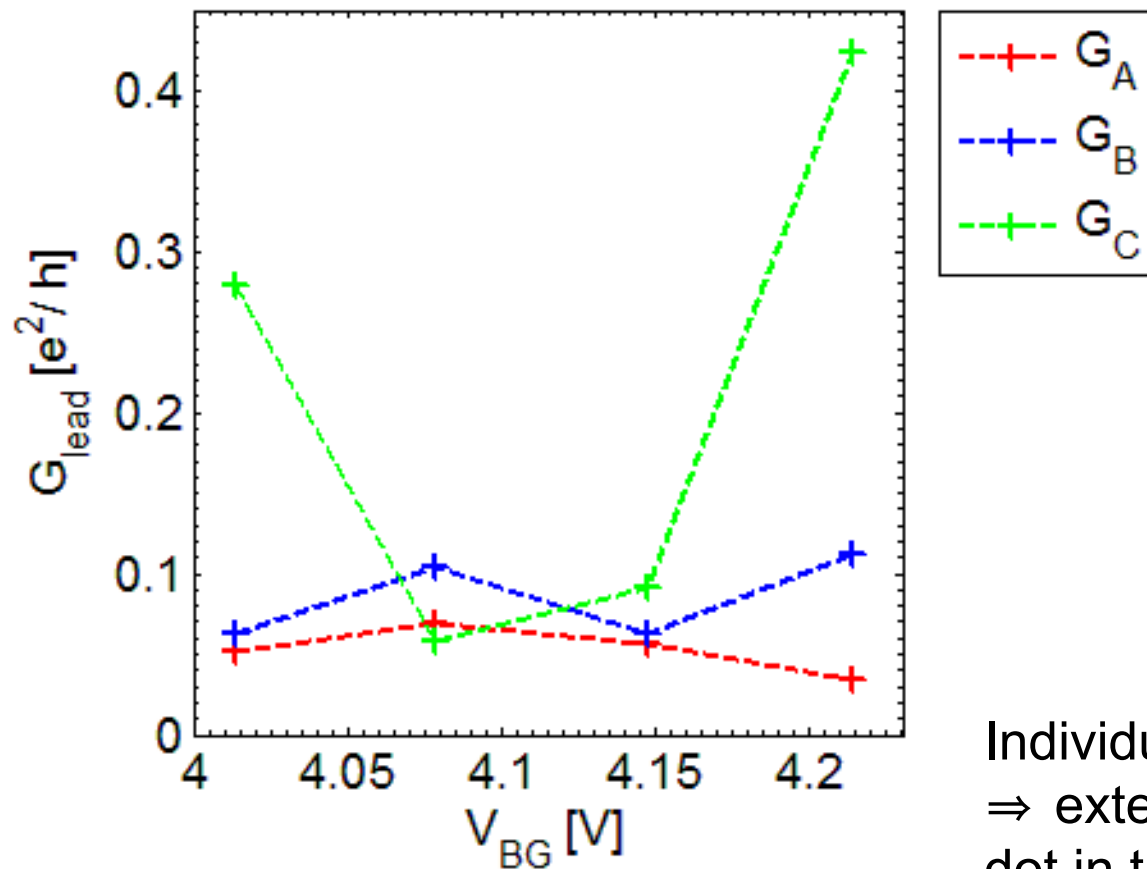
$$\begin{pmatrix} G_{11} & G_{12} & G_{13} \\ G_{21} & G_{22} & G_{23} \\ G_{31} & G_{32} & G_{33} \end{pmatrix} = \frac{1}{G_1 + G_2 + G_3} \begin{pmatrix} G_1(G_2 + G_3) & -G_1G_2 & -G_1G_3 \\ -G_1G_2 & G_2(G_1 + G_3) & -G_2G_3 \\ -G_3G_3 & -G_3G_2 & G_3(G_1 + G_2) \end{pmatrix}$$

**2-terminal sequential tunneling:**

$$G_n = \frac{e^2}{h} \frac{1}{4kT} \left( \frac{1}{\Gamma_n^S} + \frac{1}{\Gamma_n^D} \right)^{-1} \cosh^{-2} \left( \frac{\alpha_G (V_G^n - V_G)}{2kT} \right)$$

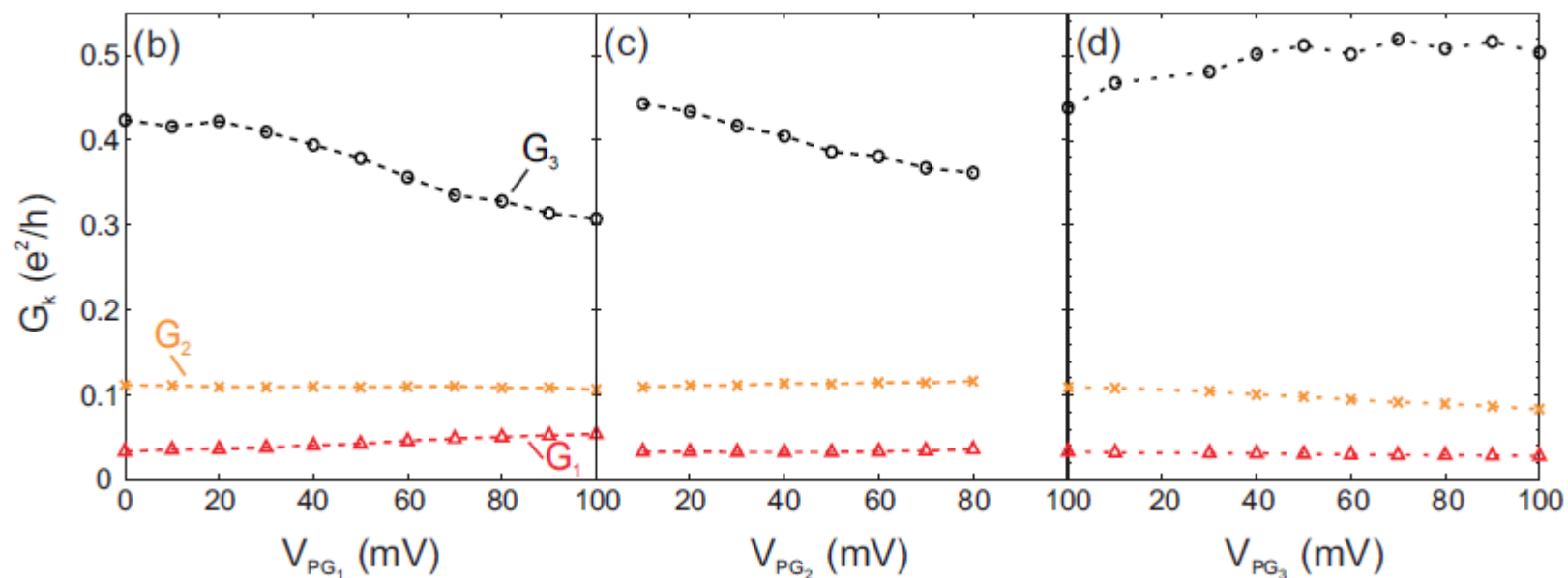
# Three-terminal dot: -> lead conductances

$$G_A, G_B, G_C = f(V_{BG})$$



Individual coupling to the leads  
⇒ extent of the wave function in the dot in the vicinity of the leads.

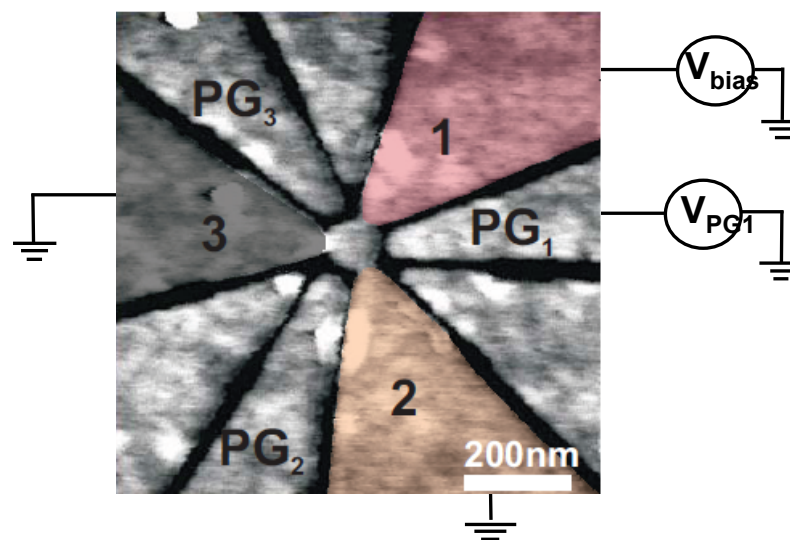
# Lateral gating



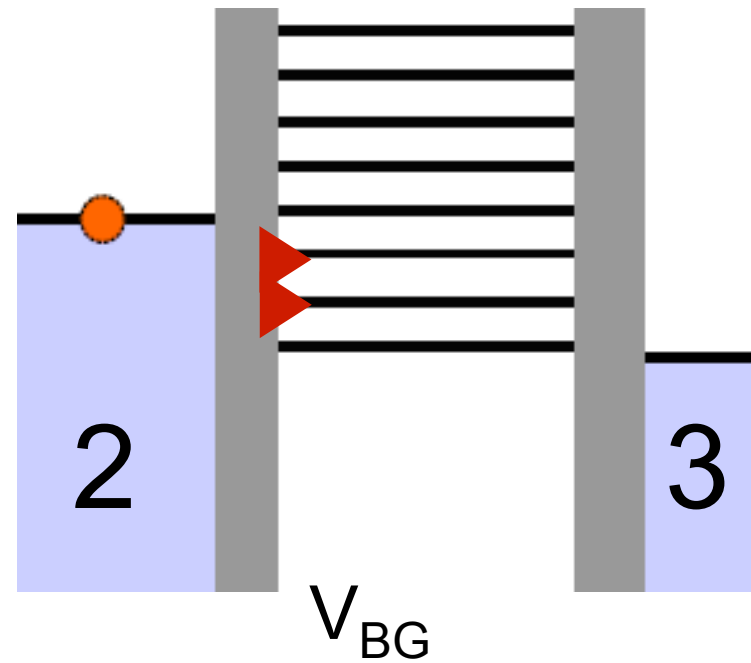
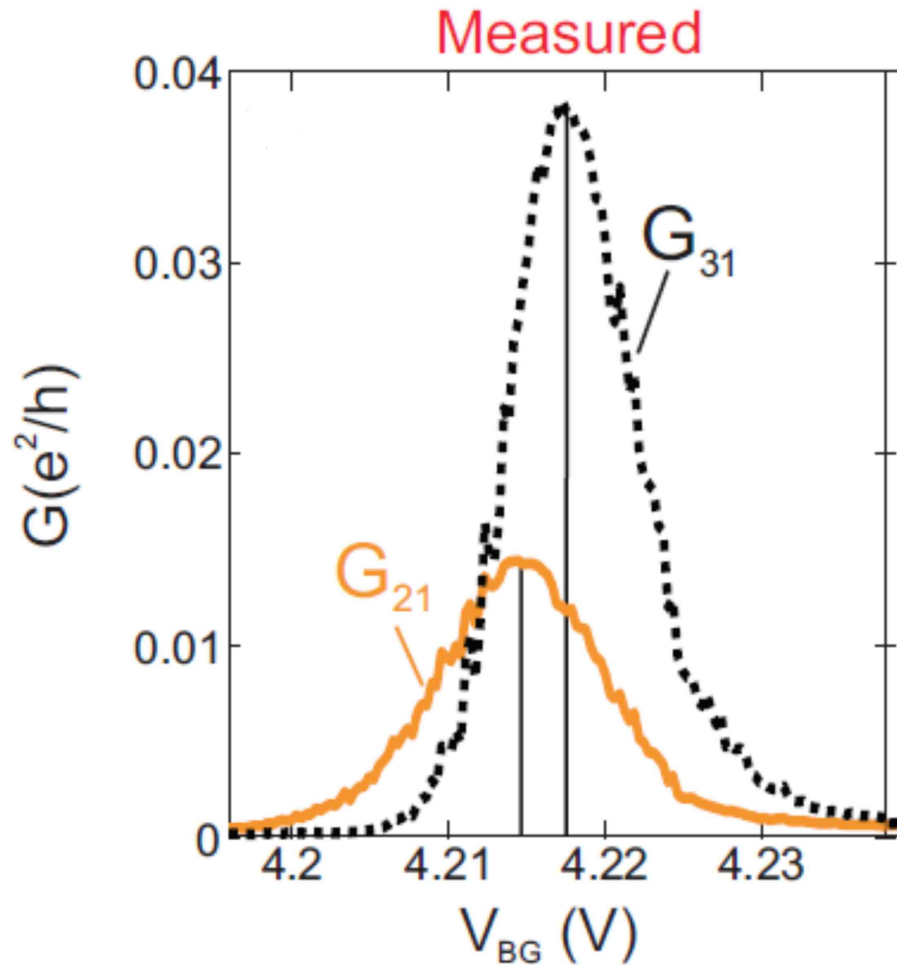
Points taken at  $V_{BG} \approx$  Peak

\* resonance

- Plunger gates seem to tune dominantly the dot.
- Homogeneous dot rather than puddles.



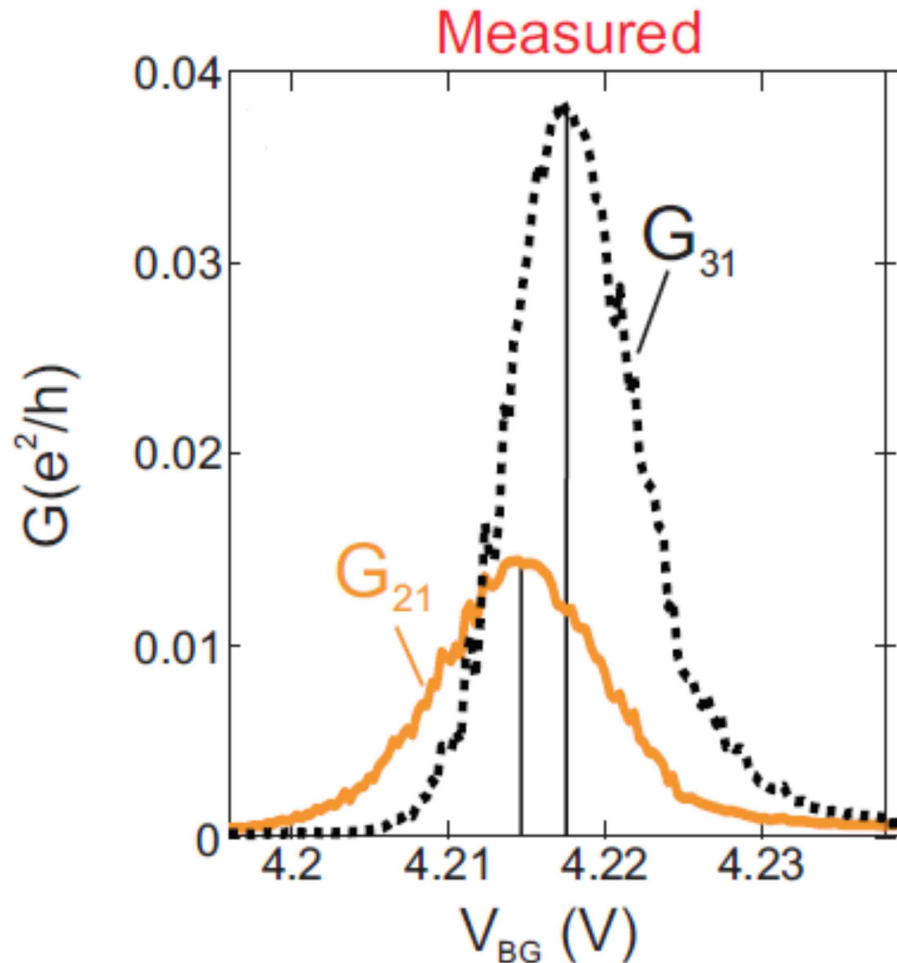
# Multi-level transport



Resonances in two leads at slightly different energies



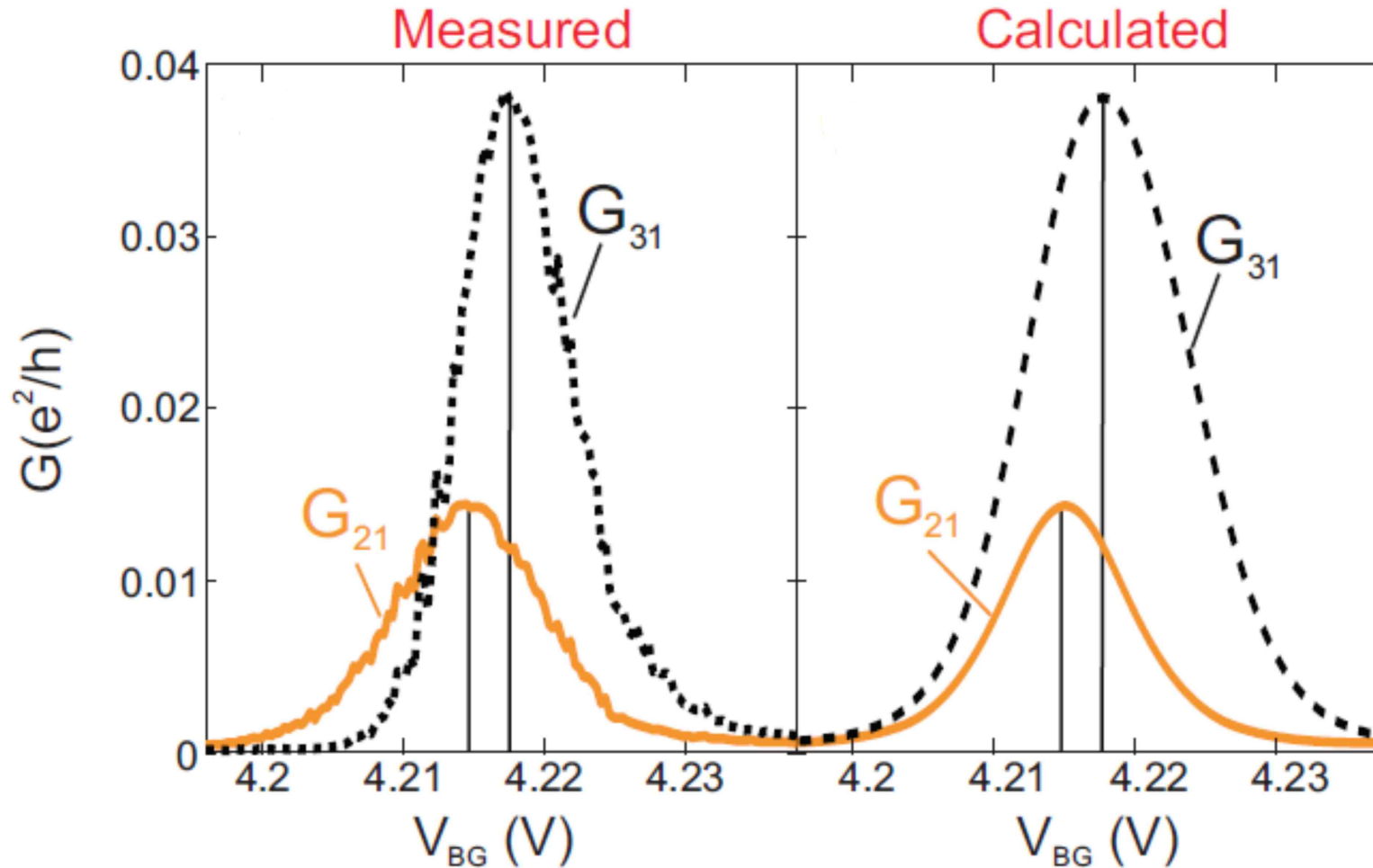
# Multi-level transport



- Rate equations
- Linearization  
(Beenakker, 1991)
- 2 contributing currents from 2 levels
- Parameters:
  - single particle level spacing
  - peak height
  - distribution of current between two levels

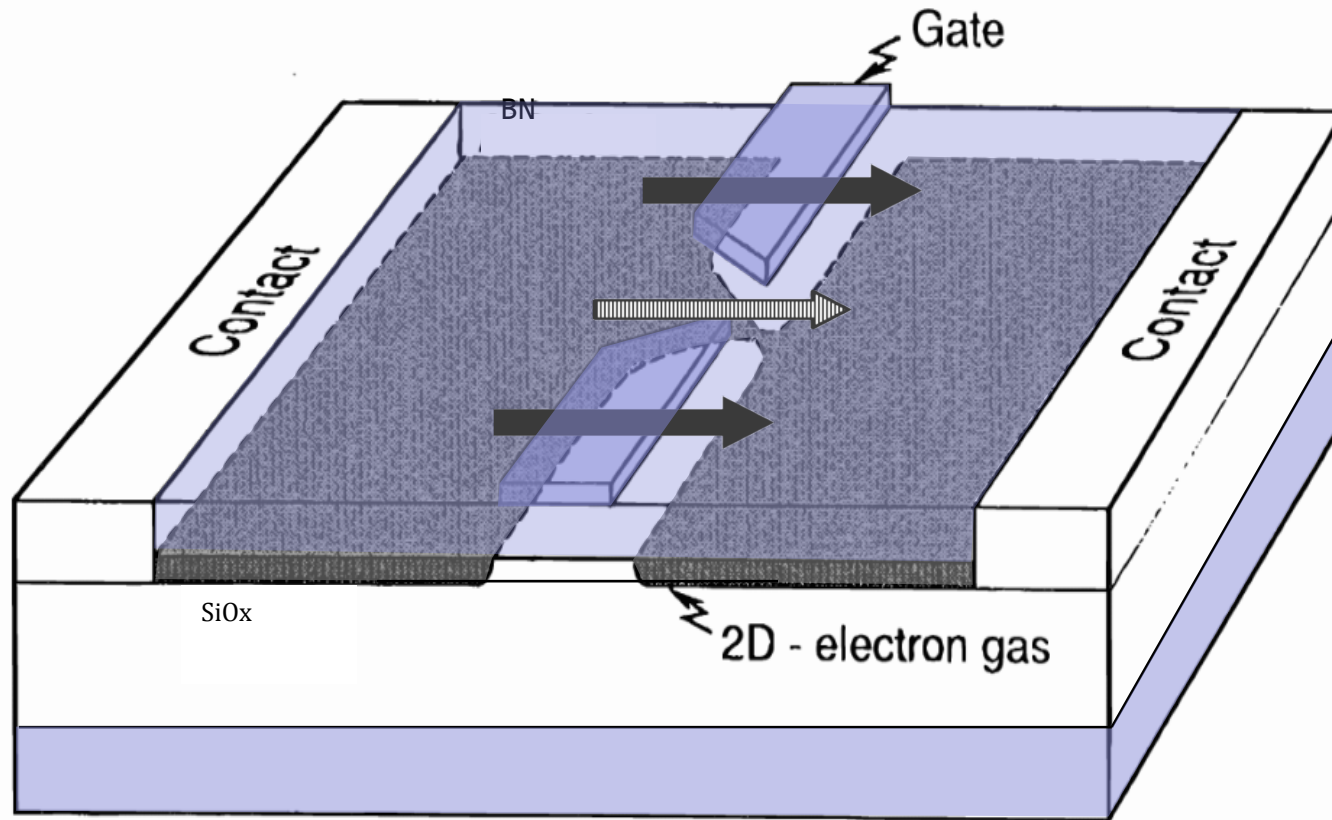
Resonances in two leads at slightly different energies

# Multi-level transport



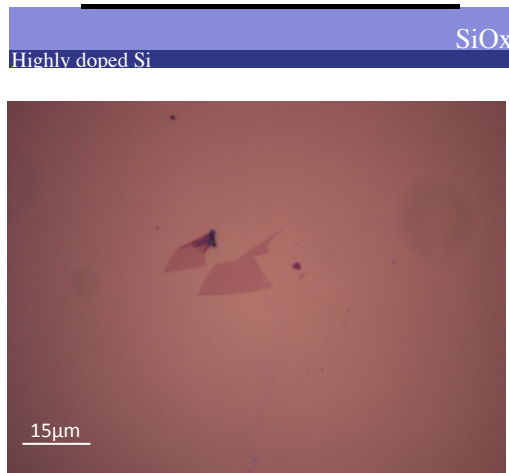
Resonances in two leads at slightly different energies

# Split-gates on bilayer graphene

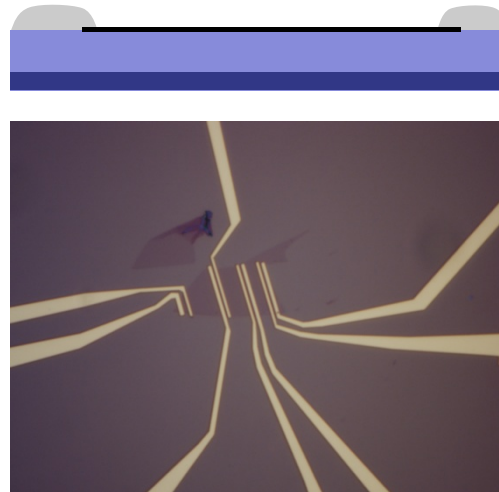


# Quantum structures on bilayer graphene

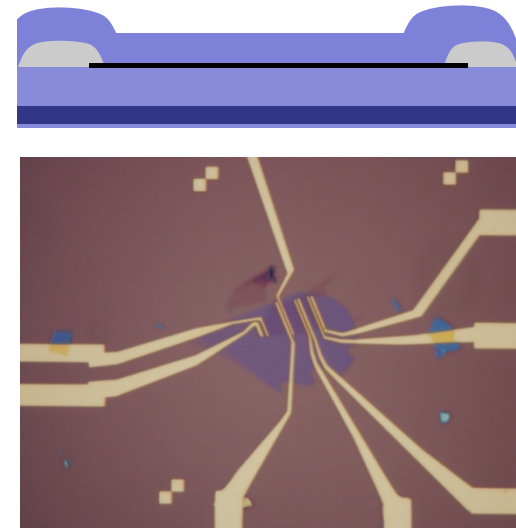
graphene deposition



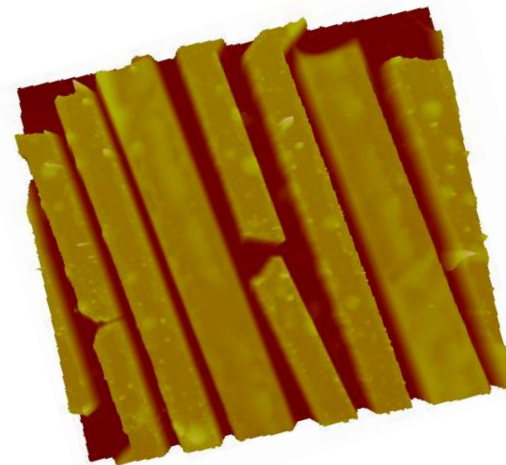
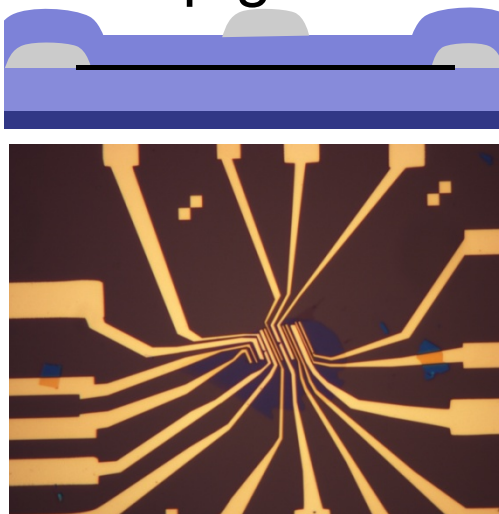
Ohmic contacts

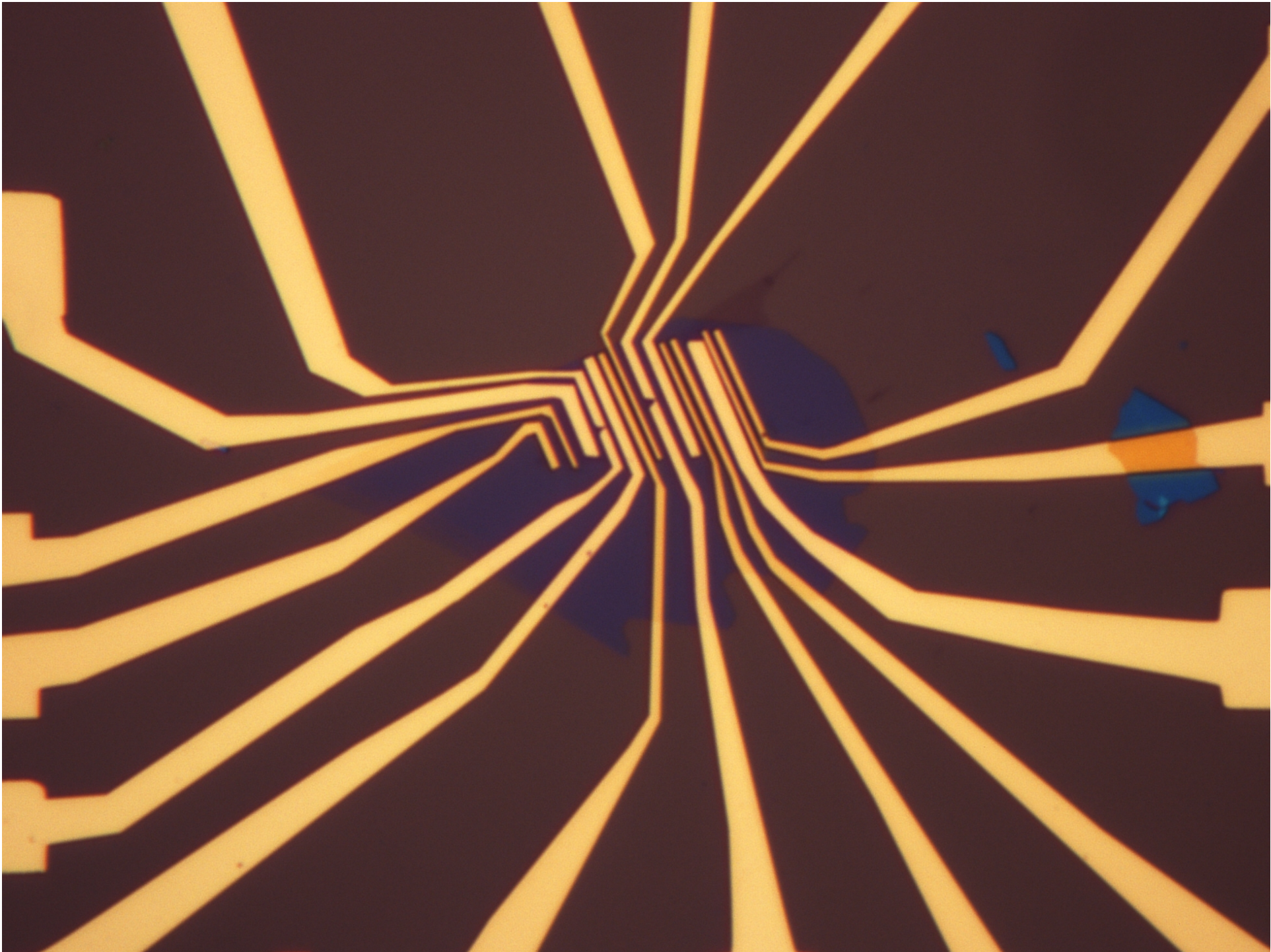


BN deposition



Top gate





Susanne Dröscher



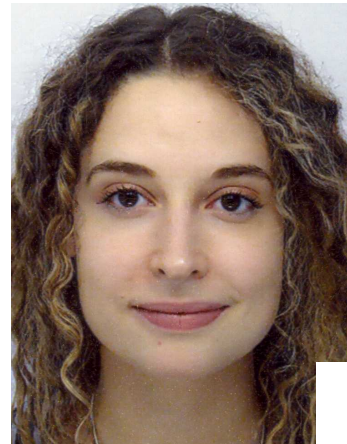
# Thank you

Constrictions: Coulomb blockade  
Multi-terminal quantum structures  
Bilayer quantum structures

Clément Barraud



Pauline Simonet



Thomas Ihn



Arnchild Jacobsen

